

High-Speed Quad Monolithic SPST CMOS Analog Switch

Features

- Fast Switching t_{ON} : 55 ns
- Low Charge Injection: 5 pC
- Low $r_{DS(on)}$: 32 Ω
- TTL/CMOS Compatible
- Low Leakage: 50 pA

Benefits

- Fast Settling Times
- Reduced Switching Glitches
- High Precision

Applications

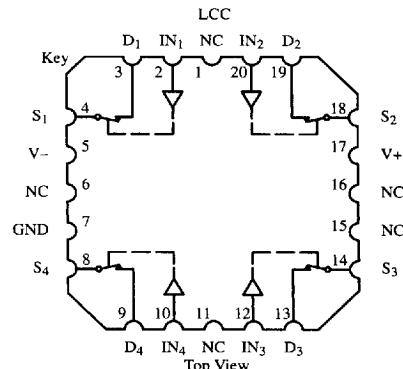
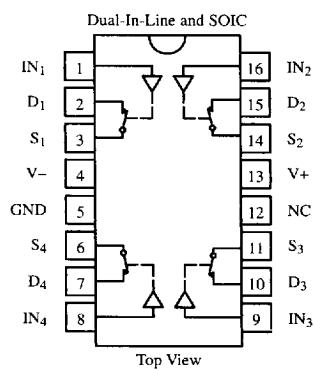
- High Speed Switching
- Sample/Hold
- Digital Filters
- Op Amp Gain Switching
- Flight Control Systems
- Automatic Test Equipment
- Choppers
- Communication Systems

Description

The DG271 high speed quad single-pole single-throw analog switch is intended for applications that require low on-resistance, low leakage currents, and fast switching speeds.

Built on Siliconix' proprietary high voltage silicon gate process to achieve superior on/off performance, each switch conducts equally well in both directions when on, and blocks up to the supply voltage when off. An epitaxial layer prevents latchup.

Functional Block Diagram and Pin Configuration



Truth Table

| Logic | Switch |
|-------|--------|
| 0 | ON |
| 1 | OFF |

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.0 V

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70043.

Siliconix
S-53750—Rev. E, 14-Jul-97

4-101

■ 8254735 0021943 2T8 ■

DG271

TEMIC

Siliconix

Ordering Information

| Temp Range | Package | Part Number |
|--------------|--------------------|-----------------|
| 0 to 70°C | 16-Pin Plastic DIP | DG271CJ |
| -40 to 85°C | 16-Pin Narrow SOIC | DG271DY |
| -55 to 125°C | 16-Pin CerDIP | DG271AK |
| | | DG271AK/883 |
| | | 5962-8671602MEA |
| | LCC-20 | DG271AZ/883 |
| | | 5962-8671602M2A |

Absolute Maximum Ratings

| | |
|---|--|
| V+ to V- | 44 V |
| GND to V- | 25 V |
| Digital Inputs ^a V _S , V _D | (V-) -2 V to (V+) +2 V or 20 mA, whichever occurs first |
| Current, Any Terminal | 30 mA |
| Peak Current, S or D | |
| (Pulsed at 1 ms, 10% duty cycle max) | 100 mA |
| Storage Temperature (AK, AZ, DY Suffix) | -65 to 150°C |
| (CJ Suffix) | -65 to 125°C |
| Power Dissipation (Package) ^b | |
| 16-Pin Plastic DIP ^c | 470 mW |
| 16-Pin Plastic Narrow SOIC ^d | 600 mW |
| 16-Pin CerDIP ^e | 900 mW |
| LCC-20 ^f | 750 mW |

Notes:

- Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC Board.
- Derate 6.5 mW/°C above 75°C
- Derate 7.6 mW/°C above 75°C
- Derate 12 mW/°C above 75°C
- Derate 10 mW/°C above 75°C

Schematic Diagram (Typical Channel)

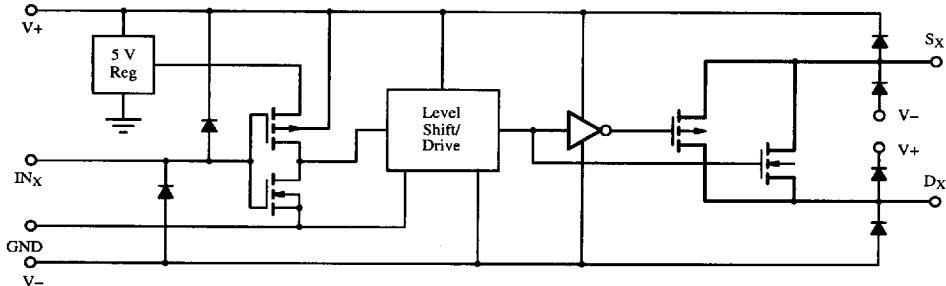


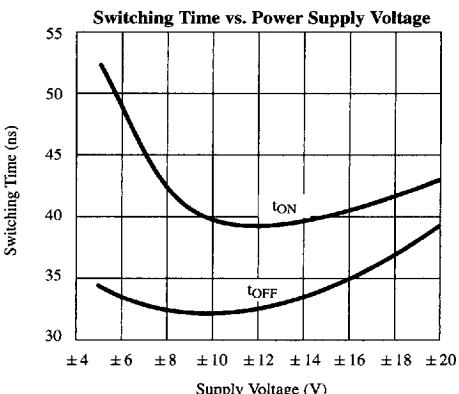
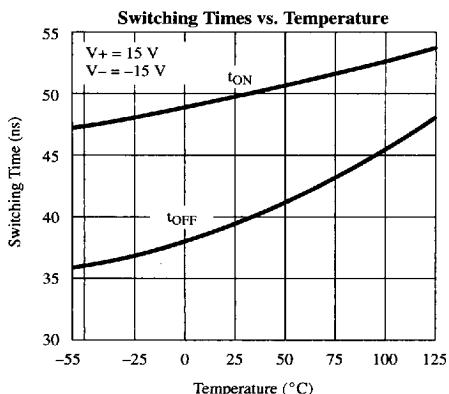
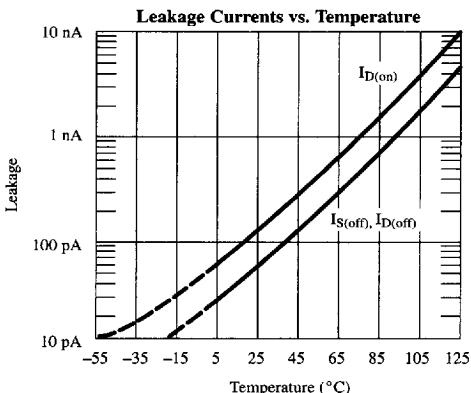
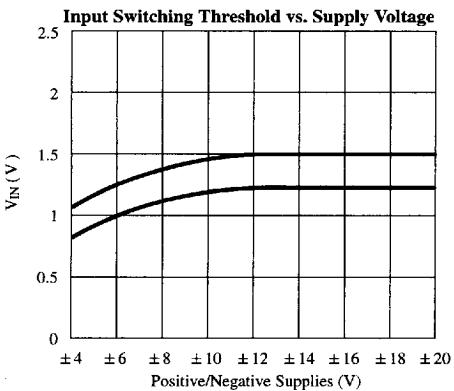
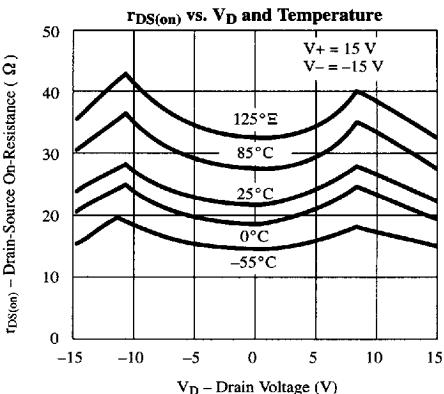
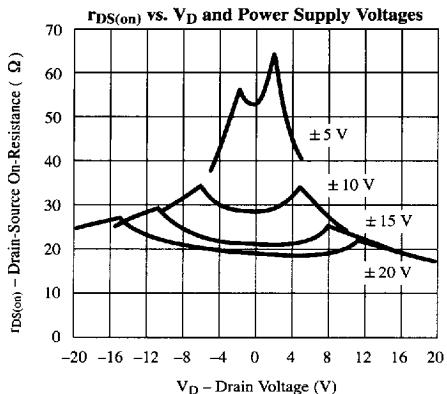
Figure 1.

Specifications^a

| Parameter | Symbol | Conditions Unless Otherwise Specified $V_+ = 15 \text{ V}$, $V_- = -15 \text{ V}$ $V_{IN} = 2.4 \text{ V}$, 0.8 V^f | Temp ^b | Typ ^c | A Suffix -55 to 125°C | | C, D Suffix 0 to 70°C -40 to 85°C | | Unit |
|----------------------------------|-------------------------|---|-------------------|------------------|--------------------------|------------------|---|------------------|------|
| | | | | | Min ^d | Max ^d | Min ^d | Max ^d | |
| Analog Switch | | | | | | | | | |
| Analog Signal Range ^e | V_{ANALOG} | | Full | | -15 | 15 | -15 | 15 | V |
| Drain-Source On-Resistance | $r_{DS(on)}$ | $I_S = 1 \text{ mA}$, $V_D = \pm 10 \text{ V}$ | Room Full | 32 | | 50 75 | | 50 75 | Ω |
| Switch Off Leakage Current | $I_{S(off)}$ | $V_D = \pm 14 \text{ V}$, $V_S = \mp 14 \text{ V}$ | Room Full | ± 0.05 | -1 -60 | 1 60 | -1 -20 | 1 20 | nA |
| | $I_{D(off)}$ | | Room Full | ± 0.05 | -1 -60 | 1 60 | -1 -20 | 1 20 | |
| Channel On Leakage Current | $I_{D(on)} + I_{S(on)}$ | $V_S = V_D = \pm 14 \text{ V}$ | Room Full | ± 0.05 | -1 -60 | 1 60 | -1 -20 | 1 20 | |
| Digital Control | | | | | | | | | |
| Input Current with Voltage High | I_{INH} | $V_{IN} = 2 \text{ V}$ | Full | 0.010 | -1 | 1 | -1 | 1 | μA |
| | | $V_{IN} = 15 \text{ V}$ | Full | 0.010 | -1 | 1 | -1 | 1 | |
| Input Current with Voltage Low | I_{INL} | $V_{IN} = 0 \text{ V}$ | Full | 0.010 | -1 | 1 | -1 | 1 | |
| Dynamic Characteristics | | | | | | | | | |
| Turn-On Time | t_{ON} | $V_S = \pm 10 \text{ V}$ See Figure 2 | Room Full | 55 | | 65 80 | | 65 80 | ns |
| Turn-Off Time | t_{OFF} | | Room Full | 50 | | 65 80 | | 65 80 | |
| Charge Injection | Q | $C_L = 1 \text{ nF}$, $V_S = 0 \text{ V}$ $V_{gen} = 0 \text{ V}$, $R_{gen} = 0 \Omega$ See Figure 3 | Room | -5 | | | | | pC |
| Source Off Capacitance | $C_{S(off)}$ | $V_S = 0 \text{ V}$, $V_{IN} = 5 \text{ V}$ $f = 1 \text{ MHz}$ | Room | 8 | | | | | pF |
| Drain Off Capacitance | $C_{D(off)}$ | | Room | 8 | | | | | |
| Channel On Capacitance | $C_{D(on)}$ | $V_D = V_S = 0 \text{ V}$, $V_{IN} = 0 \text{ V}$ | Room | 30 | | | | | |
| Off Isolation | OIRR | $C_L = 10 \text{ pF}$, $R_L = 1 \text{ kΩ}$ $f = 100 \text{ kHz}$ See Figures 4 and 5 | Room | 85 | | | | | dB |
| Crosstalk | X _{TALK} | | Room | 100 | | | | | |
| Supply | | | | | | | | | |
| Positive Supply Current | I ₊ | All Channels On or Off | Room Full | 5.5 | | 7.5 9 | | 7.5 9 | mA |
| Negative Supply Current | I ₋ | | Room Full | -3.4 | -6 -8 | | -6 -8 | | |

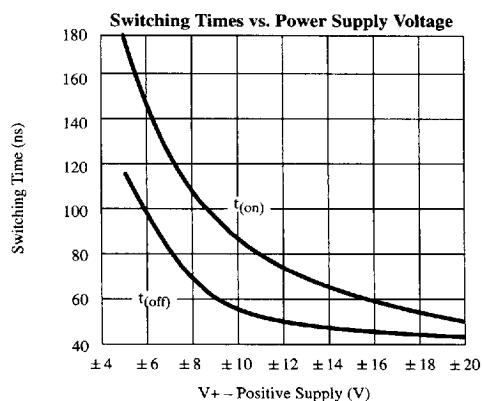
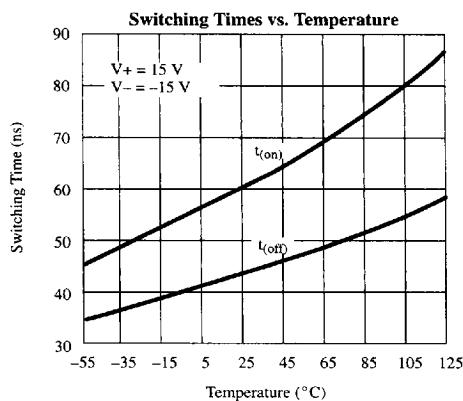
Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25°C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

DG271**Typical Characteristics**

■ 8254735 0021946 T07 ■

Typical Characteristics (Cont'd)



Test Circuits

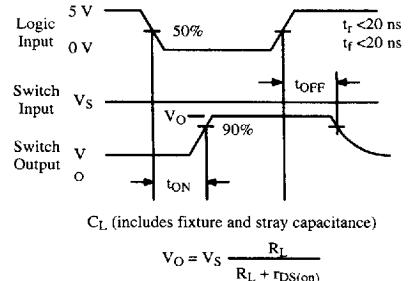
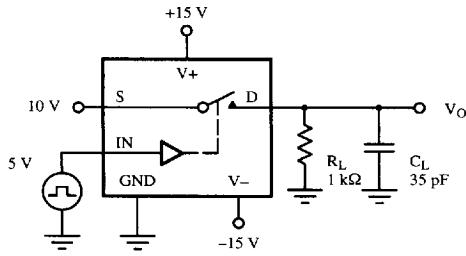


Figure 2. Switching Time